

11DQ15 SCHOTTKY RECTIFIER

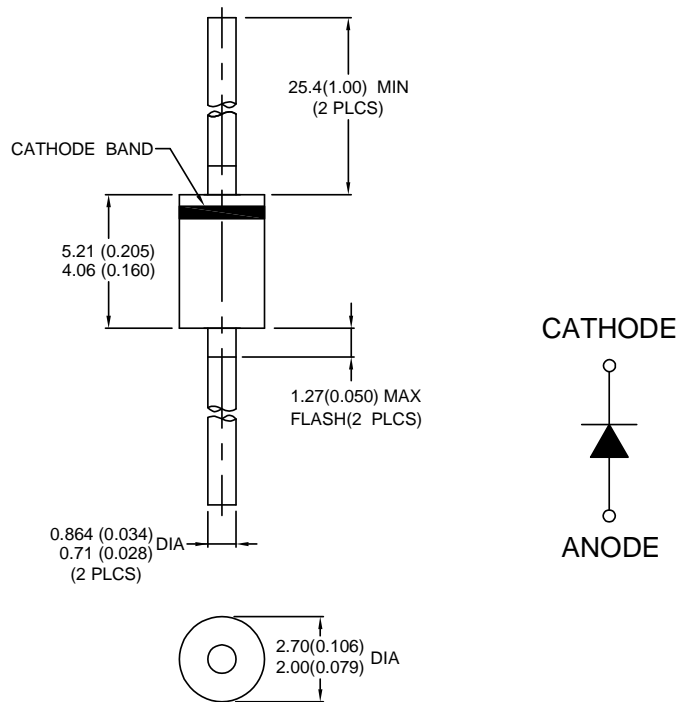
Applications:

- Switching power supply
- Converters
- Free-Wheeling diodes
- Reverse battery protection

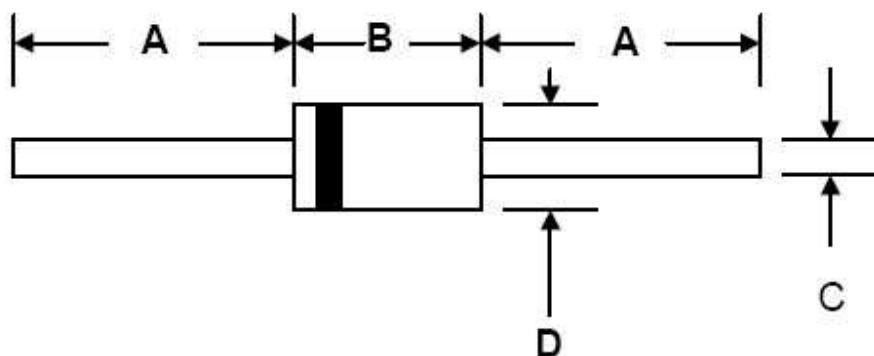
Features:

- Low profile, axial leaded outline
- High purity, high temperature epoxy encapsulation for enhanced mechanical strength and moisture resistance
- Very low forward voltage drop
- High frequency operation
- Guard ring for enhanced ruggedness and long term reliability
- Green Products in Compliance with the RoHS Directive
- This is a Pb - Free Device
- All SMC parts are traceable to the wafer lot
- Additional testing can be offered upon request

Mechanical Dimensions: In mm / Inches



OPTION 1



SYMBOL	DIMENSIONS	
	MIN.	MAX.
A	26.3	26.8
B	4.95	5.05
C	0.68	0.72
D	2.55	2.65

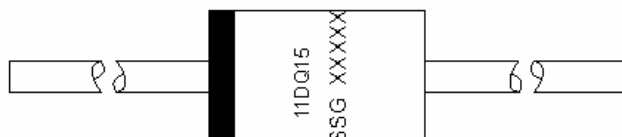
OPTION 2(HY)

DO-41



Technical Data
Data Sheet N0655, Rev. A

Marking Diagram:



Where XXXXX is YYWWL

11DQ15 = Part Name
SSG = SSG
YY = Year
WW = Week
L = Lot Number

Cautions: Molding resin
Epoxy resin UL:94V-0

Ordering Information:

Device	Package	Shipping
11DQ15	DO-41 (Pb-Free)	5000pcs / reel

For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification.



Maximum Ratings:

Characteristics	Symbol	Condition	Max.	Units
Peak Inverse Voltage	V_{RWM}	-	150	V
Max. Average Forward Current	$I_{F(AV)}$	50% duty cycle @ $T_C = 75\text{ }^\circ\text{C}$, rectangular wave form	1.0	A
Max. Peak One Cycle Non-Repetitive Surge Current	I_{FSM}	8.3 ms, half Sine pulse	20	A

Electrical Characteristics:

Characteristics	Symbol	Condition	Max.	Units
Max. Forward Voltage Drop*	V_{F1}	@1 A, Pulse, $T_J = 25\text{ }^\circ\text{C}$	0.86	V
	V_{F2}	@1 A, Pulse, $T_J = 125\text{ }^\circ\text{C}$	0.70	V
Max. Reverse Current *	I_{R1}	@ $V_R = \text{Rated } V_R$, Pulse, $T_J = 25\text{ }^\circ\text{C}$	0.5	mA
	I_{R2}	@ $V_R = \text{Rated } V_R$, Pulse, $T_J = 125\text{ }^\circ\text{C}$	1.0	mA
Max. Junction Capacitance	C_T	@ $V_R = 5\text{ V}$, $T_C = 25\text{ }^\circ\text{C}$ $f_{SIG} = 1\text{ MHz}$	35	pF
Typical Series Inductance	L_S	Measured lead to lead 5 mm from package body	8.0	nH
Max. Voltage Rate of Change (Rated V_R)	dv/dt		10,000	V/ μs

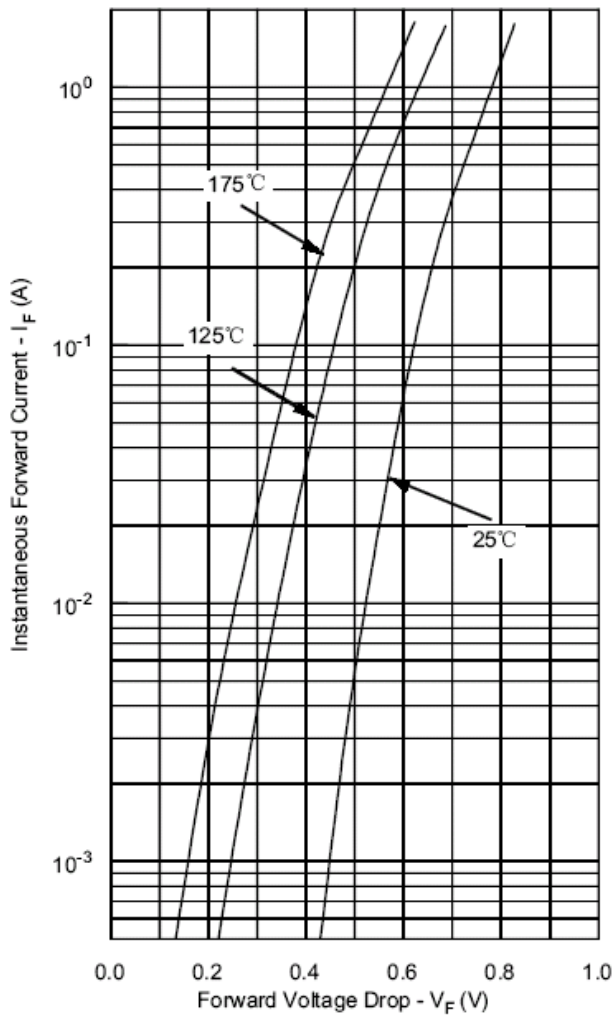
* Pulse Width < 300 μs , Duty Cycle < 2%

Thermal-Mechanical Specifications:

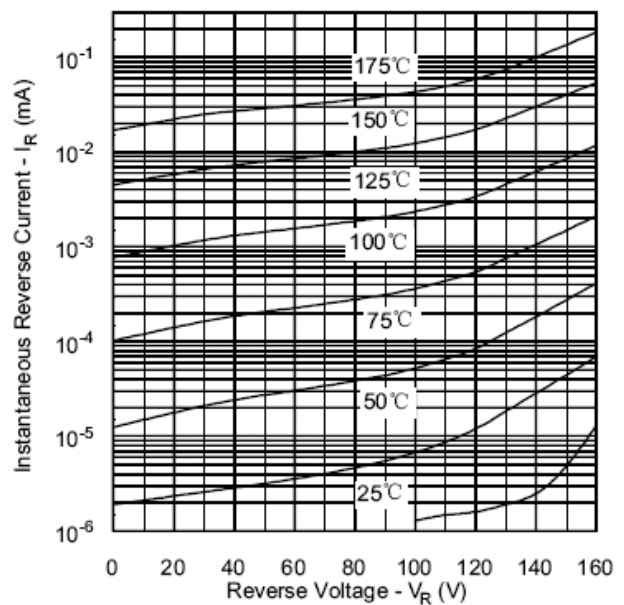
Characteristics	Symbol	Condition	Specification	Units
Max. Junction Temperature	T_J	-	-40 to +175	$^\circ\text{C}$
Max. Storage Temperature	T_{stg}	-	-40 to +175	$^\circ\text{C}$
Maximum Thermal Resistance Junction to Ambient	$R_{\theta JA}$	DC operation	100	$^\circ\text{C/W}$
Typical Thermal Resistance Junction to Lead	$R_{\theta JL}$	DC operation	81	$^\circ\text{C/W}$
Approximate Weight	wt	-	0.33	g
Case Style	DO-41(DO-204AL)			



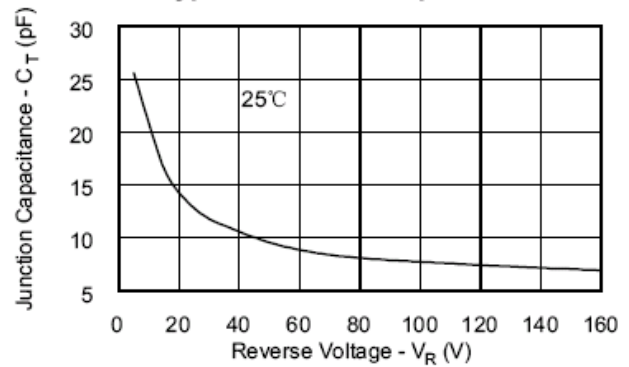
Typical Forward Characteristics



Typical Reverse Characteristics



Typical Junction Capacitance





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